

# Ruslan Ivanov

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

12  
papers

136  
citations

7  
h-index

11  
g-index

16  
ext. papers

158  
ext. citations

3.1  
avg, IF

2.16  
L-index

#	Paper	IF	Citations
12	T2SL development for space at IRnova: from eSWIR to VLWIR <b>2019</b> ,		2
11	QWIPs are keeping their promises <b>2019</b> ,		1
10	Direct Measurement of Nanoscale Lateral Carrier Diffusion: Toward Scanning Diffusion Microscopy. <i>ACS Photonics</i> , <b>2018</b> , 5, 528-534	6.3	12
9	Influence of shallow versus deep etching on dark current and quantum efficiency in InAs/GaSb superlattice photodetectors and focal plane arrays for long wavelength infrared detection. <i>Infrared Physics and Technology</i> , <b>2018</b> , 95, 158-163	2.7	5
8	LWIR QWIPs at IRnova for next generation polarimetric imaging. <i>Infrared Physics and Technology</i> , <b>2018</b> , 95, 177-182	2.7	3
7	Scanning near-field microscopy of carrier lifetimes in m-plane InGaN quantum wells. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 031109	3.4	12
6	Polarization-Resolved Near-Field Spectroscopy of Localized States in m-Plane In <sub>x</sub> Ga <sub>1-x</sub> N/GaN Quantum Wells. <i>Physical Review Applied</i> , <b>2017</b> , 7,	4.3	12
5	Influence of well width fluctuations on recombination properties in semipolar InGaN quantum wells studied by time- and spatially-resolved near-field photoluminescence. <i>Optical Materials Express</i> , <b>2017</b> , 7, 3116	2.6	10
4	Properties of near-field photoluminescence in green emitting single and multiple semipolar (202°) plane InGaN/GaN quantum wells. <i>Optical Materials Express</i> , <b>2016</b> , 6, 39	2.6	5
3	Impact of carrier localization on radiative recombination times in semipolar (202°) plane InGaN/GaN quantum wells. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 211109	3.4	20
2	High spatial uniformity of photoluminescence spectra in semipolar (202°) plane InGaN/GaN quantum wells. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 023111	2.5	25
1	Highly polarized photoluminescence and its dynamics in semipolar (202°) InGaN/GaN quantum well. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 111113	3.4	29